

# BCR08AM-14A

# Triac

Low Power Use

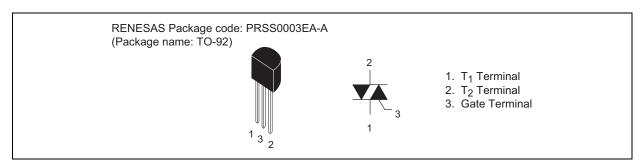
REJ03G1200-0200 Rev.2.00 Nov 30, 2007

### **Features**

I<sub>T (RMS)</sub>: 0.8 A
 V<sub>DRM</sub>: 700 V

I<sub>FGT I</sub>, I<sub>RGT I</sub>, I<sub>RGT III</sub>: 5 mA
 Planar Passivation Type

### **Outline**



### **Applications**

Washing machine, electric fan, air cleaner, other general purpose control applications

### **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	
Faranieter	Syllibol	14		
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	700	V	
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	840	V	

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	0.8	А	Commercial frequency, sine full wave 360° conduction, Tc = 67°C
Surge on-state current	I <sub>TSM</sub>	8	А	60 Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	0.26	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60 Hz, surge on-state current
Peak gate power dissipation	P <sub>GM</sub>	1	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.1	W	
Peak gate voltage	$V_{GM}$	6	V	
Peak gate current	I <sub>GM</sub>	0.5	А	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
Mass	_	0.23	g	Typical value

Notes: 1. Gate open.

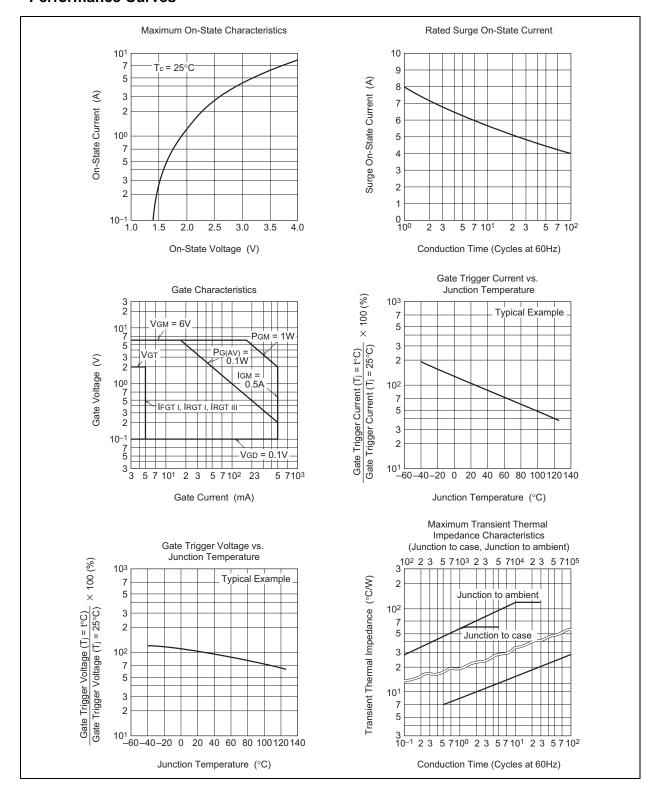
### **Electrical Characteristics**

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>		_	1.0	mA	Tj = 125°C, V <sub>DRM</sub> applied
On-state voltage		$V_{TM}$		_	2.0	V	Tc = 25°C, I <sub>TM</sub> = 1.2 A, Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGT_{I}}$		_	2.0	V	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	$V_{RGT_{\mathrm{I}}}$		_	2.0	V	$R_G = 330 \Omega$
	III	$V_{RGT_{III}}$		_	2.0	V	
Gate trigger current <sup>Note2</sup>	I	$I_{\text{FGT}_{\text{I}}}$	_	_	5	mA	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	$I_{RGTI}$	_	_	5	mA	$R_G = 330 \Omega$
	III	$I_{RGTIII}$	_	_	5	mA	
Gate non-trigger voltage		$V_{GD}$	0.1	_	_	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-c)</sub>	_	_	50	°C/W	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>		(dv/dt)c	0.5	_	_	V/μs	Tj = 125°C

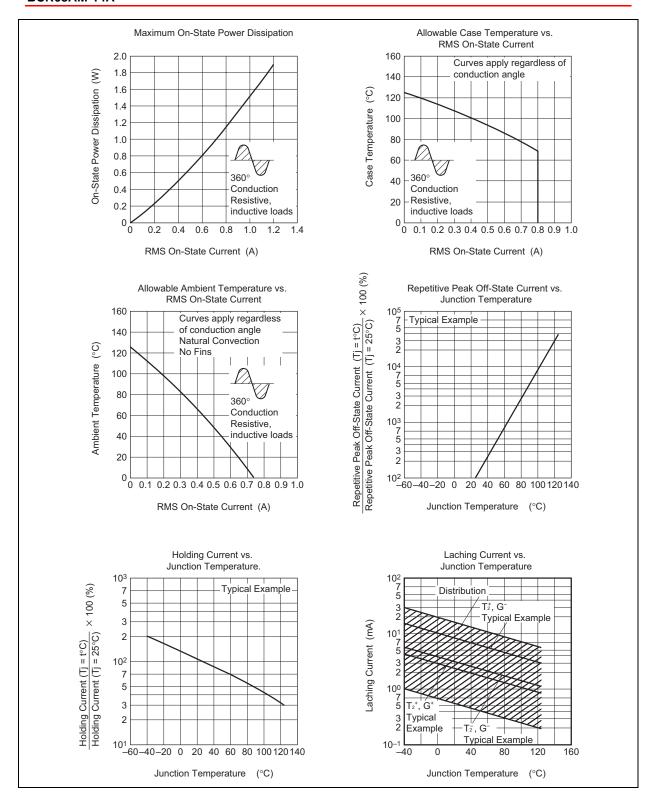
- Notes: 2. Measurement using the gate trigger characteristics measurement circuit.
  - 3. Case temperature is measured at the  $T_2$  terminal 1.5 mm away from the molded case.
  - 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

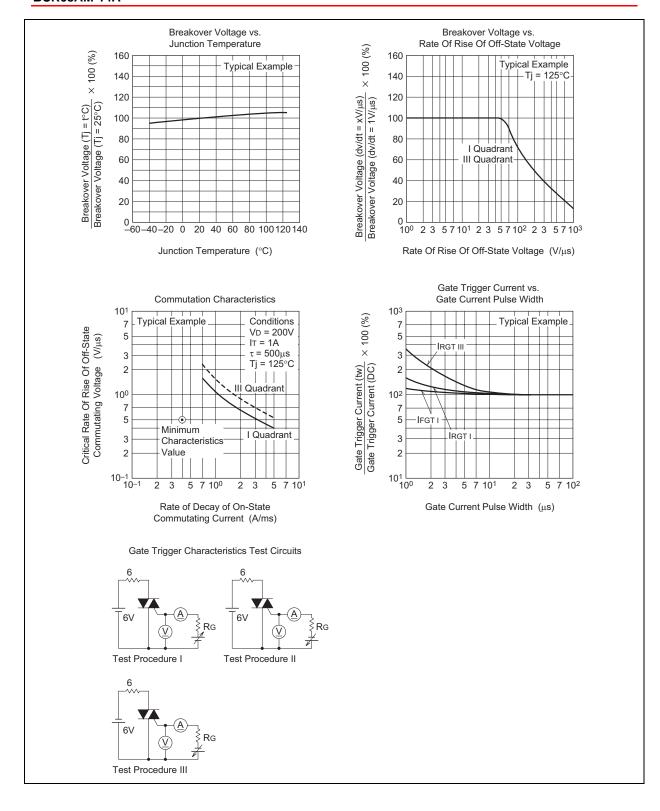
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C	Supply → Time
2. Rate of decay of on-state commutating current (di/dt)c = - 0.4 A/ms	Main Current (di/dt)c → Time
3. Peak off-state voltage V <sub>D</sub> = 400 V	Main Voltage (dv/dt)c

### **Performance Curves**

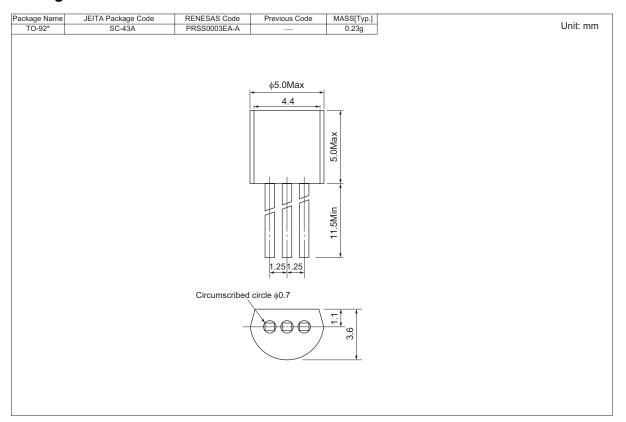


Downloaded from Elcodis.com electronic components distributor





# **Package Dimensions**



## **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	500	Type name	BCR08AM-14A
Lead form	Vinyl sack	500	Type name – Lead forming code	BCR08AM-14A-A6
Form A8	Taping	2000	Type name – TB	BCR08AM-14A-TB

Note: Please confirm the specification about the shipping in detail.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

  Notes:

  1. This document is provided for reference purposes only so that Penesas customers may select the appropriate Renesas products for their use. Renesas neither makes in the reference purposes only so that Penesas customers may select the appropriate Renesas products for their use. Renesas neither makes are all to the source of the product of the reseas of the information in this document nor grants any license to any intellectual property rights or any other rights of Renesas or any third party with respect to the information in this document nor grants any license to any intellectual property or other rights arising out of the use of any information in this document, including, but not limited to, product data, diagrams, charts, programs, algorithms, and application circuit examples.

  3. You should not use the products or the technology described in this document for the purpose of military applications such as the development of waspons of mass and application circuit examples, is current as of the date this document in included in this document such as product data, diagrams, charts, programs, algorithms, and application circuit examples, is current as of the date this document is issued. Such information however, is subject to change without any prior notice. Before purchasing or using any Renesas products itself in this document, but all information in included in this document, but application control laws and products of the products of the products of the date this document, but application and careful attention to additional and different information in the date this document, but applications on the latest product information where the subject to change without any prior notice. Before purchase repeated the subject of the products of



### **RENESAS SALES OFFICES**

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd. 1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510